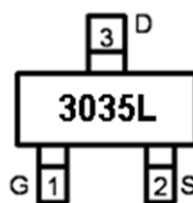
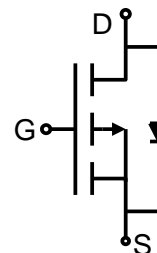


Main Product Characteristics:

V_{DSS}	-30V
$R_{DS(on)}$	22m Ω (typ.)
I_D	-6A ^①


SOT23-3

Marking and Pin Assignments

Schematic Diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature


Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating: @ $T_A=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Max.	Units
I_D @ $TC = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ^①	-6	A
I_D @ $TC = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ^①	-5	
I_{DM}	Pulsed Drain Current ^②	-30	
P_D @ $TC = 25^\circ\text{C}$	Power Dissipation ^③	2	W
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

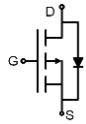
Thermal Resistance

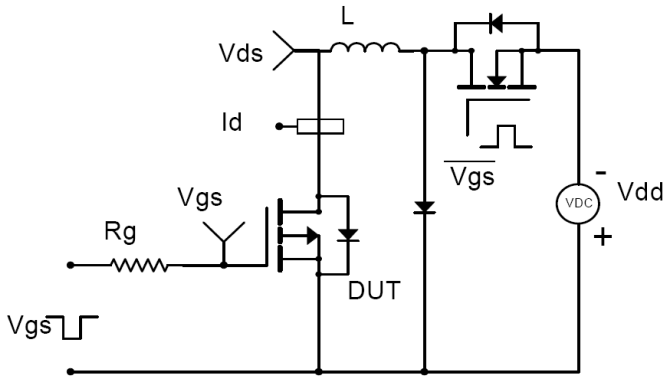
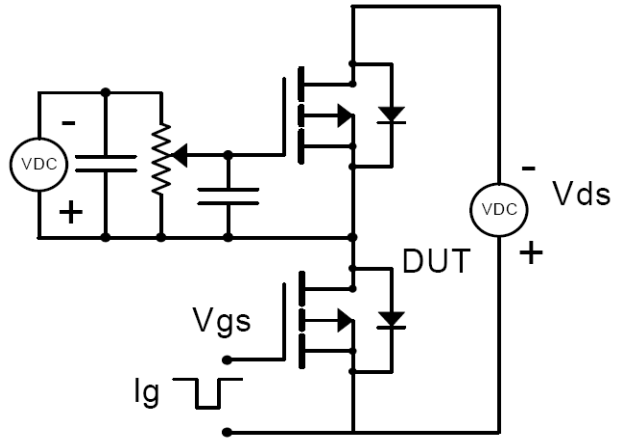
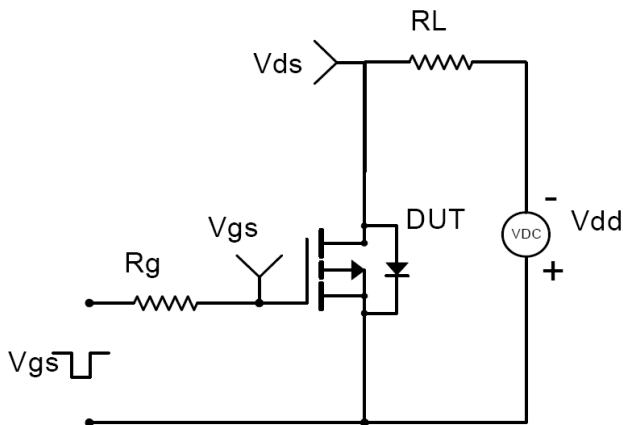
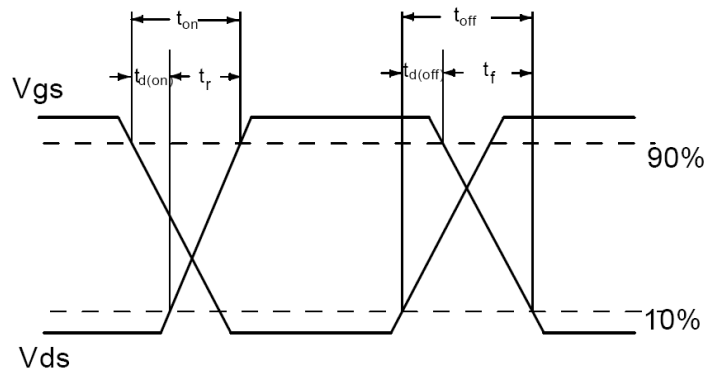
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10\text{s}$) ^④	—	62.5	$^\circ\text{C}/\text{W}$

Electrical Characterizes @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	22	30	m Ω	$V_{GS}=-10V, I_D = -5.4A$
		—	33	40		$V_{GS}=-4.5V, I_D = -4.6A$
$V_{GS(th)}$	Gate threshold voltage	-1.2	—	-2.5	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
		—	-1.45	—		$T_J = 125^{\circ}\text{C}$
I_{DSS}	Drain-to-Source leakage current	—	—	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
		—	—	-50		$T_J = 125^{\circ}\text{C}$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
Q_g	Total gate charge	—	10	—	nC	$I_D = -6A,$ $V_{DS}=-15V,$ $V_{GS} = -4.5V$
Q_{gs}	Gate-to-Source charge	—	3	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	4	—		
$t_{d(on)}$	Turn-on delay time	—	10.5	—	ns	$V_{GS}=-10V, V_{DS}=-15V,$ $R_{GEN}=3\Omega, R_L=2.7\Omega$
t_r	Rise time	—	5.4	—		
$t_{d(off)}$	Turn-Off delay time	—	25	—		
t_f	Fall time	—	8.5	—		
C_{iss}	Input capacitance	—	1300	—	pF	$V_{GS} = 0V,$ $V_{DS} = -25V,$ $f = 1\text{MHz}$
C_{oss}	Output capacitance	—	150	—		
C_{riss}	Reverse transfer capacitance	—	132	—		

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode) ①	—	—	-6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	-30	A	
V_{SD}	Diode Forward Voltage	—	-0.82	-1.2	V	$I_S=-4.3A, V_{GS}=0V$

Test circuits and Waveforms
EAS Test Circuit:

Gate Charge Test Circuit:

Switching Time Test Circuit:

Switch Waveforms:

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$

Typical Electrical and Thermal Characteristics

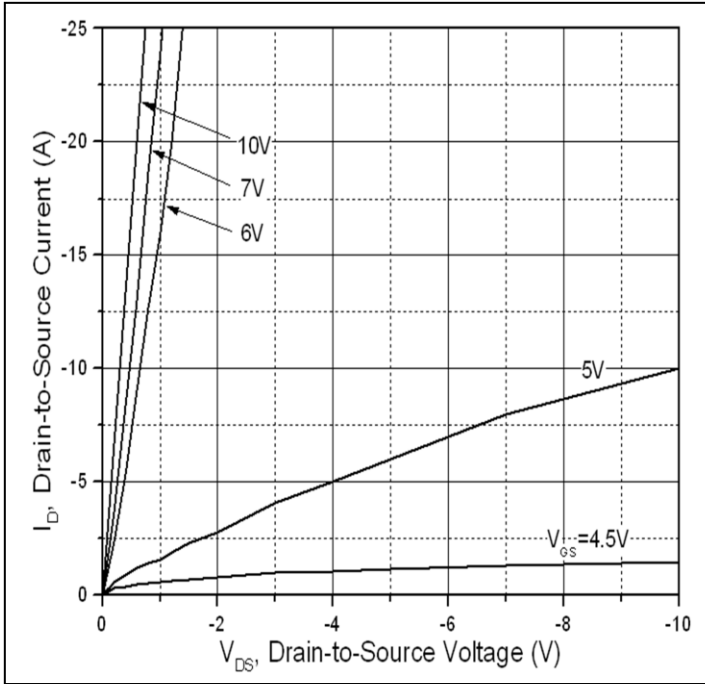


Figure 1. Typical Output Characteristics

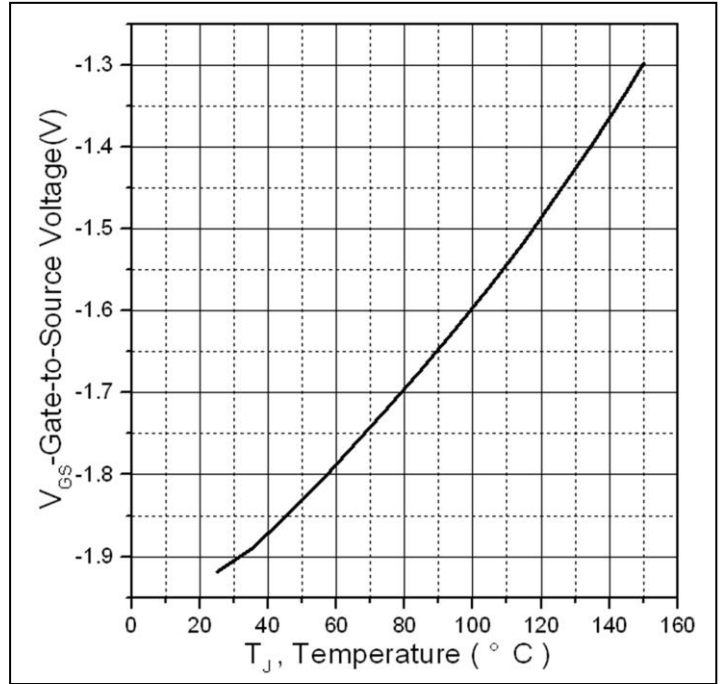


Figure 2. Gate to Source Cut-off Voltage

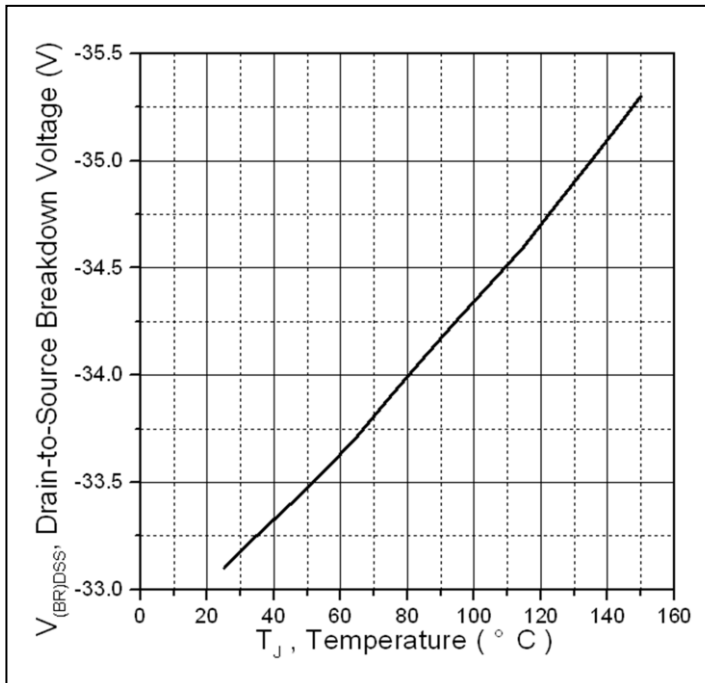


Figure 3. Drain-to-Source Breakdown Voltage vs. Junction Temperature

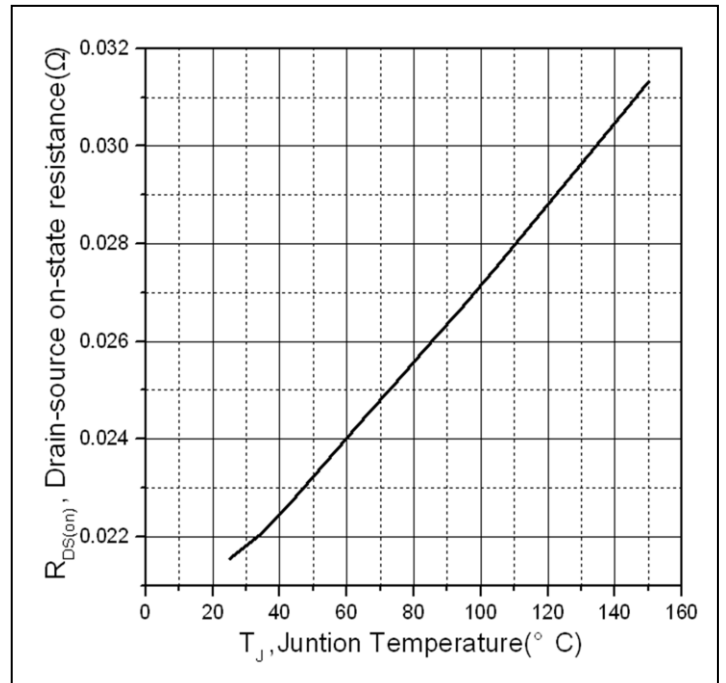


Figure 4. Normalized On-Resistance vs. Junction Temperature

Typical Electrical and Thermal Characteristics

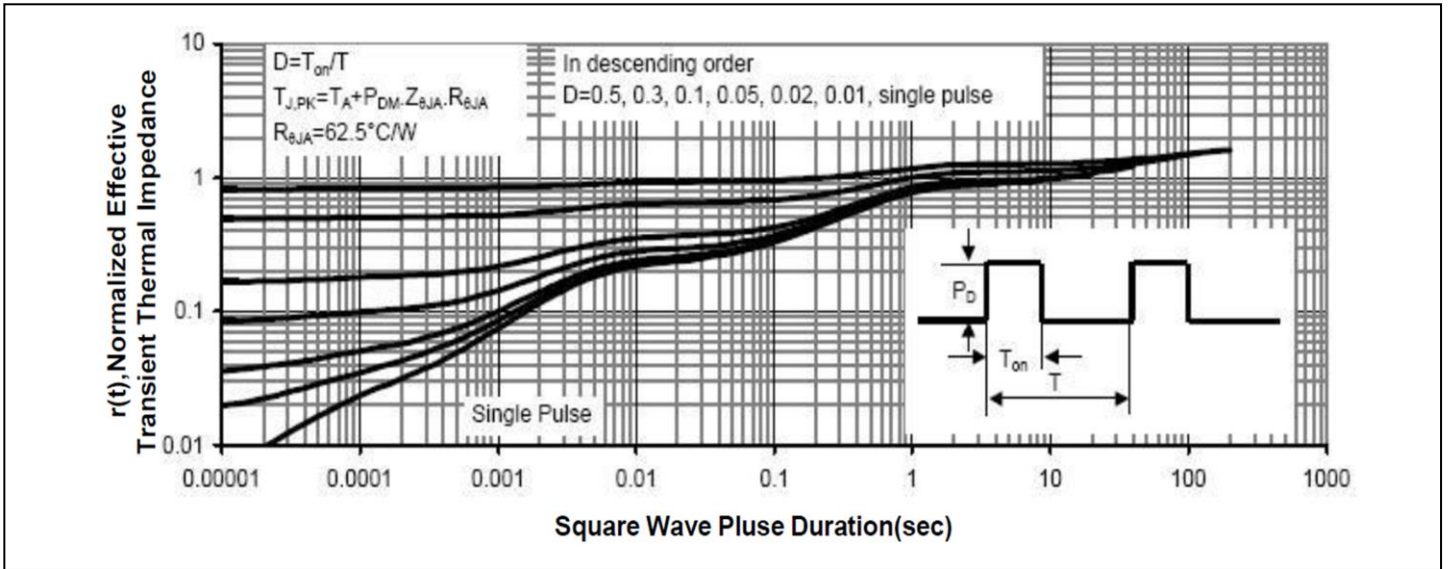


Figure5. Maximum Effective Transient Thermal Impedance

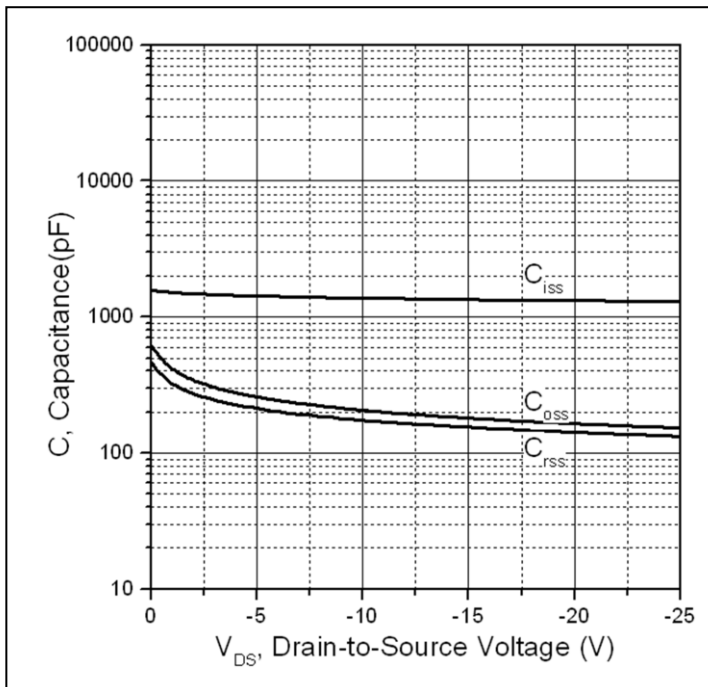
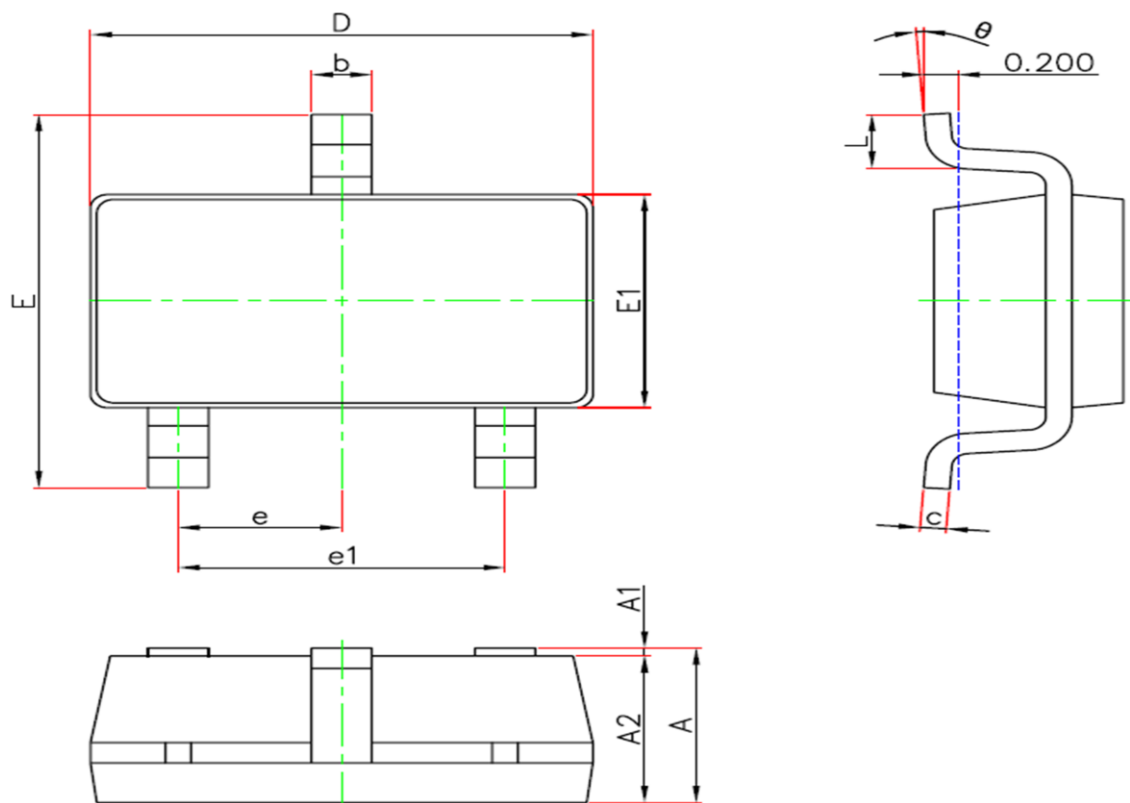


Figure 6. Typical Capacitance vs. Drain-to-Source Voltage

Mechanical Data:


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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